ABSTRACT

A nonvolatile semiconductor storing device according to the present invention comprises a block replacing means for replacing a defective block with a redundant block when a memory block in a memory array is the defective block. The block replacing means includes an address translation circuit 10 for converting an inputted external block address into an internal block address by inverting an address bit corresponding to dissident of each address bit between a defective block address of the defective block and a redundant block address among address bits of the inputted external block address, and each of the memory blocks 5 is selected based on the internal block address after the translation of the external block address inputted from outside by the address translation circuit 10.